

PBSM5240PF

40 V, 2 A PNP low V_{CEsat} (BISS) transistor with N-channel Trench MOSFET

Rev. 2 — 20 April 2011

Product data sheet

1. Product profile

1.1 General description

Combination of PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor and N-channel Trench MOSFET. The device is housed in a leadless medium power SOT1118 Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Loadswitch
- Power management
- Power switches (e.g. motors, fans)
- Battery-driven devices
- Charging circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PNP low V_{CEsat} (BISS) transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I_C	collector current		[1]	-	-1.8	A
I_{CRM}	repetitive peak collector current		[1][5]	-	-2	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	[1]	-	-3	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -500$ mA; $I_B = -50$ mA	[2]	-	240 340	m Ω



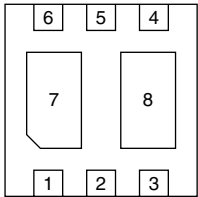
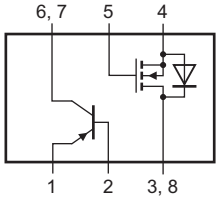
Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
N-channel Trench MOSFET						
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ °C}$	-	-	30	V
V_{GS}	gate-source voltage	$T_{amb} = 25\text{ °C}$	-	-	± 8	V
I_D	drain current	$T_{amb} = 25\text{ °C};$ $V_{GS} = 10\text{ V}$	[3]	-	0.66	A
$R_{DS(on)}$	drain-source on-state resistance	$T_j = 25\text{ °C}; V_{GS} = 4.5\text{ V};$ $I_D = 0.2\text{ A}$	[4]	-	370 580	m Ω

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [2] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [4] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.01$.
- [5] Pulse test: $t_p \leq 20\text{ ms}; \delta \leq 0.10$.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter	 <p>Transparent top view</p>	 <p>017aaa079</p>
2	base		
3	drain		
4	source		
5	gate		
6	collector		
7	collector		
8	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSM5240PF	HUSON6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 × 2 × 0.65 mm	SOT1118

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSM5240PF	1G

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

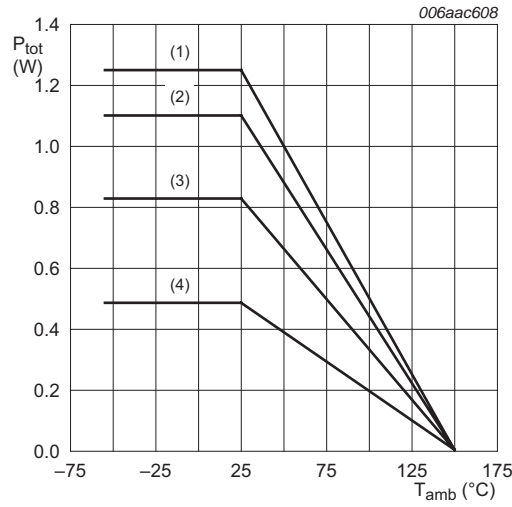
Symbol	Parameter	Conditions	Min	Max	Unit
PNP low V_{CEsat} (BISS) transistor					
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I_C	collector current		[1]	-1.8	A
I_{CRM}	repetitive peak collector current		[1][4]	-2	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	[1]	-3	A
I_B	base current		[1]	-300	mA
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	[1]	-1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	1.1	W
			[2]	1.25	W
N-channel Trench MOSFET					
V_{DS}	drain-source voltage	$T_{amb} = 25$ °C	-	30	V
V_{DG}	drain-gate voltage	$T_{amb} = 25$ °C; $R_{GS} = 20$ k Ω	-	30	V
V_{GS}	gate-source voltage	$T_{amb} = 25$ °C	-	± 8	V
I_D	drain current	$V_{GS} = 10$ V	[3]		
		$T_{amb} = 25$ °C	-	660	mA
		$T_{amb} = 100$ °C	-	420	mA
I_{DM}	peak drain current	$T_{amb} = 25$ °C; single pulse; $t_p \leq 10$ μ s	-	3.56	A
P_{tot}	total power dissipation	$T_{amb} = 25$ °C	[3]	760	mW
Source-drain diode					
I_S	source current	$T_{amb} = 25$ °C	-	660	mA
Per device					
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-55	+150	°C
T_{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

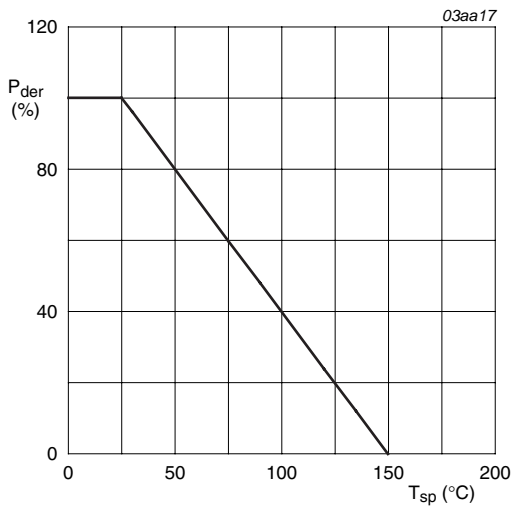
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[4] Pulse test: $t_p \leq 20$ ms; $\delta \leq 0.10$.



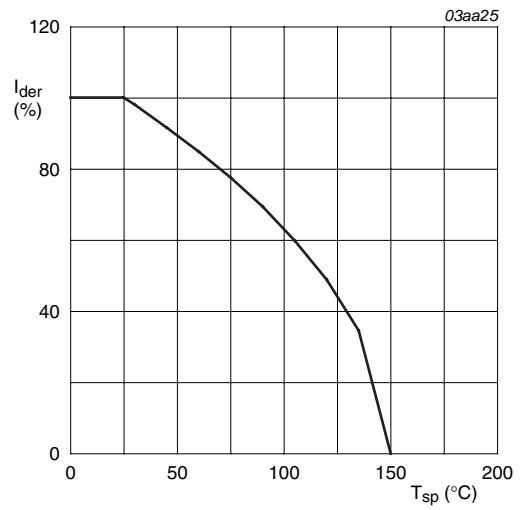
- (1) FR4 PCB, 4-layer copper, mounting pad for collector 1 cm²
- (2) FR4 PCB, single-sided copper, mounting pad for collector 6 cm²
- (3) FR4 PCB, single-sided copper, mounting pad for collector 1 cm²
- (4) FR4 PCB, single-sided copper, standard footprint

Fig 1. BISS transistor: Power derating curves



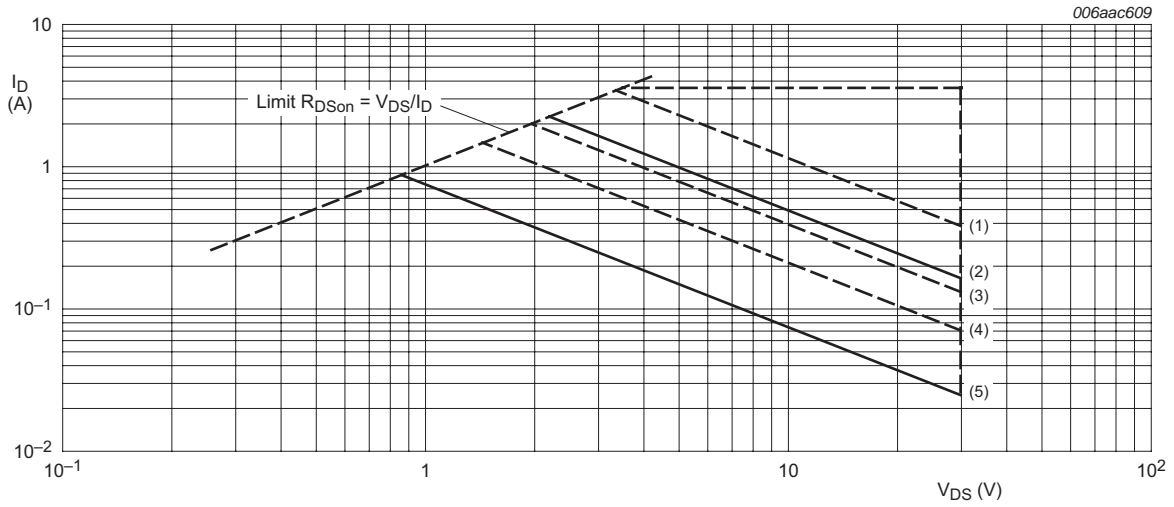
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

Fig 2. MOSFET: Normalized total power dissipation as a function of solder point temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 3. MOSFET: Normalized continuous drain current as a function of solder point temperature



- I_{DM} = single pulse
- (1) $t_p = 1$ ms
 - (2) DC; $T_{sp} = 25$ °C
 - (3) $t_p = 10$ ms
 - (4) $t_p = 100$ ms
 - (5) DC; $T_{amb} = 25$ °C; drain mounting pad 1 cm²

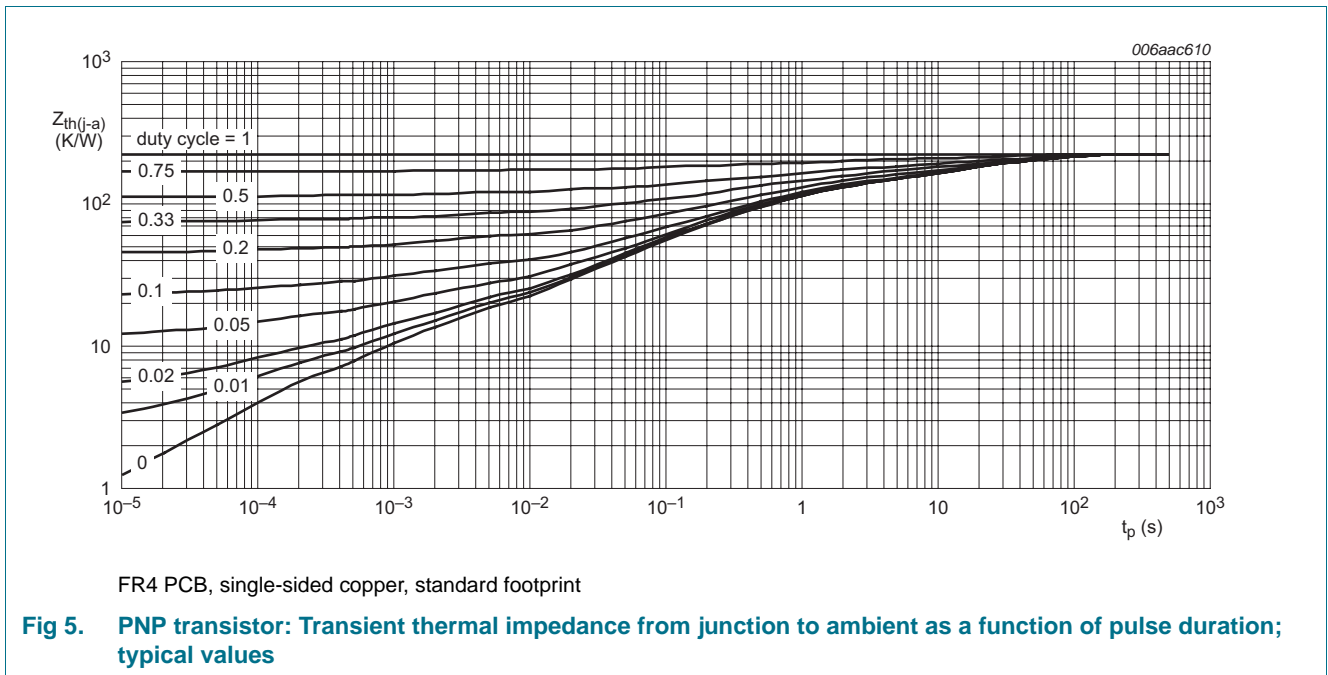
Fig 4. MOSFET: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
PNP low V_{CEsat} (BISS) transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	100	K/W
N-channel Trench MOSFET							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[3]	-	-	165	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



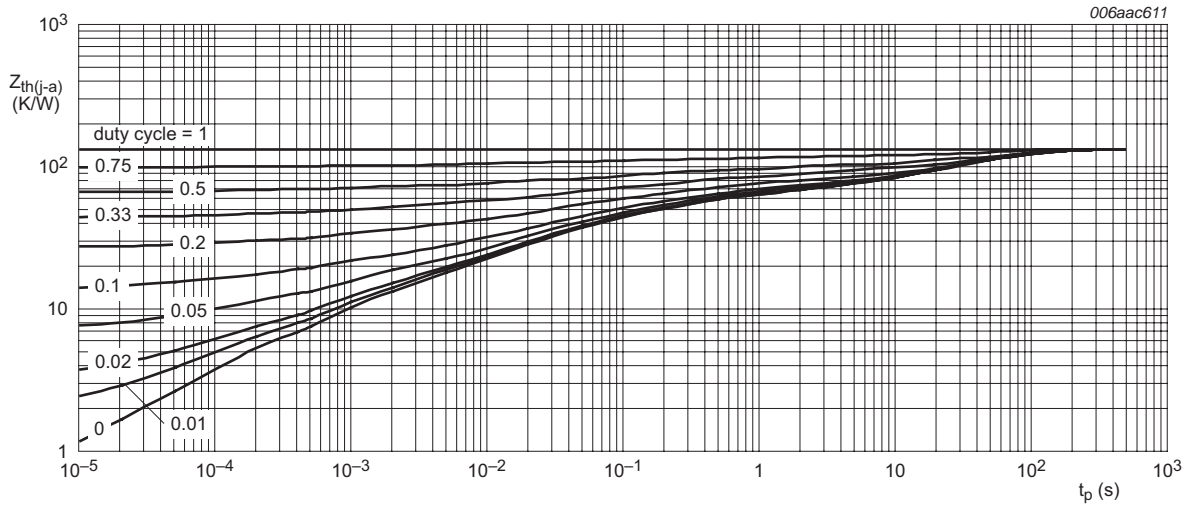


Fig 6. PNP transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

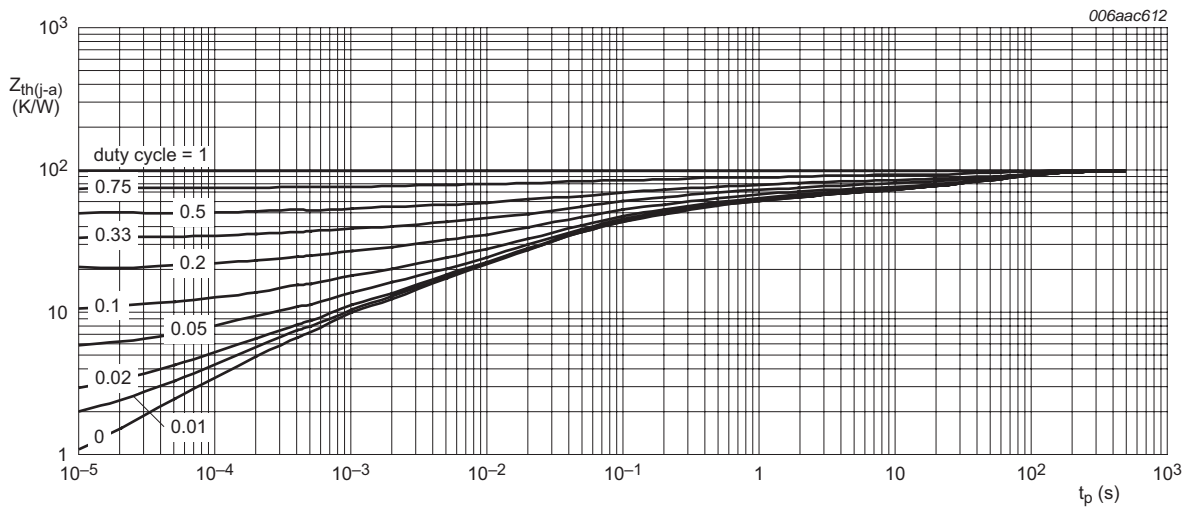
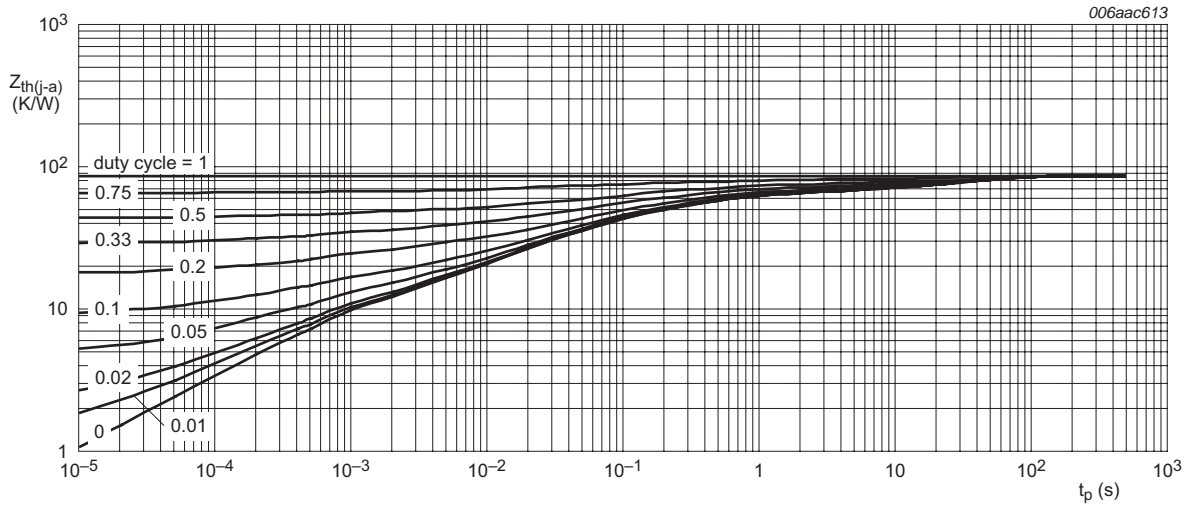
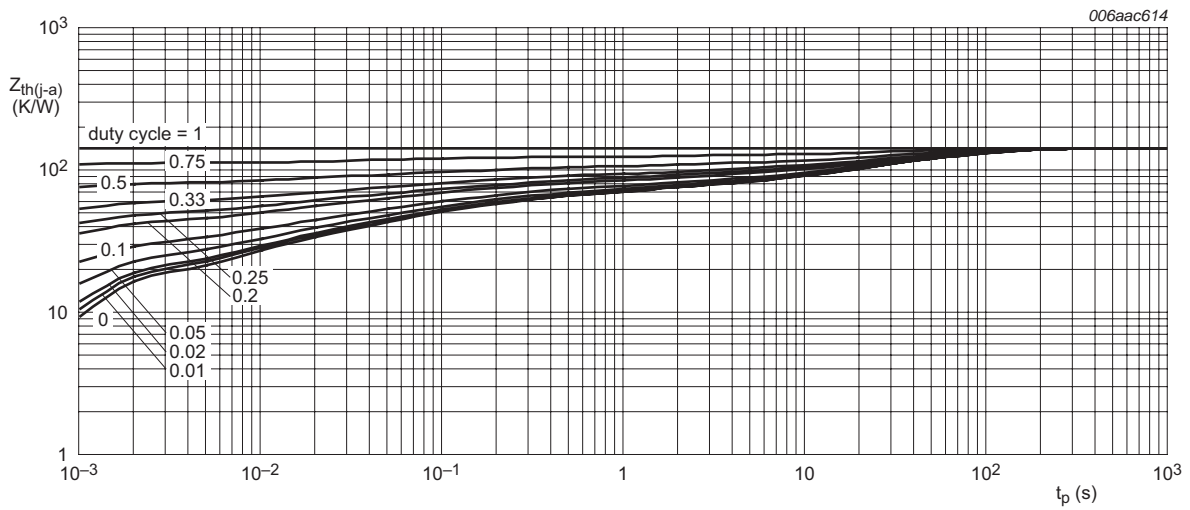


Fig 7. PNP transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, mounting pad for collector 1 cm²

Fig 8. PNP transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, mounting pad for drain 1 cm²

Fig 9. MOSFET: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

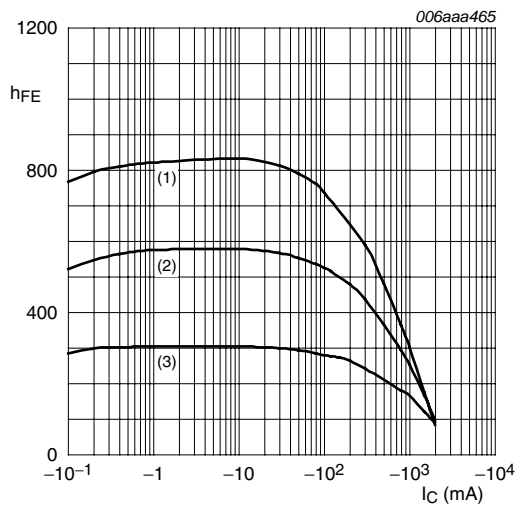
7. Characteristics

Table 7. Characteristics for PNP low V_{CEsat} transistor

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

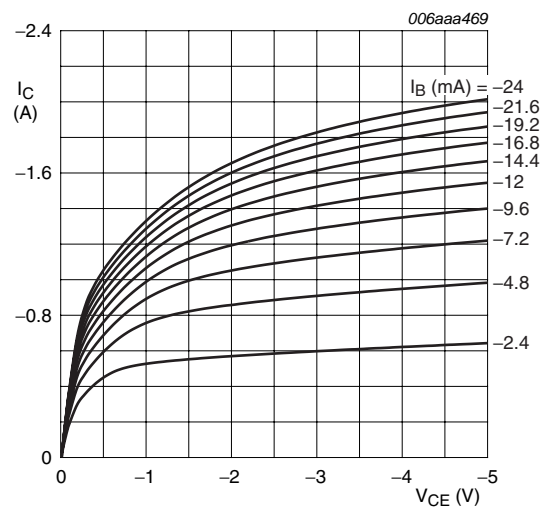
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
I_{CBO}	collector-base cut-off current	$V_{CB} = -40\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA	
		$V_{CB} = -40\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-50	μA	
I_{CEO}	collector-emitter cut-off current	$V_{CE} = -30\text{ V}; I_B = 0\text{ A}$	-	-	-100	nA	
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA	
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}$	[1]				
		$I_C = -1\text{ mA}$	300	-	-		
		$I_C = -100\text{ mA}$	300	-	800		
		$I_C = -500\text{ mA}$	200	-	-		
		$I_C = -1\text{ A}$	140	-	-		
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	[1]	-	-85	-140	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1]	-	-120	-170	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1]	-	-200	-310	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1]	-	240	340	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1]	-	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	[1]	-	-	-1	V
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	150	-	-		MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	12		pF

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.



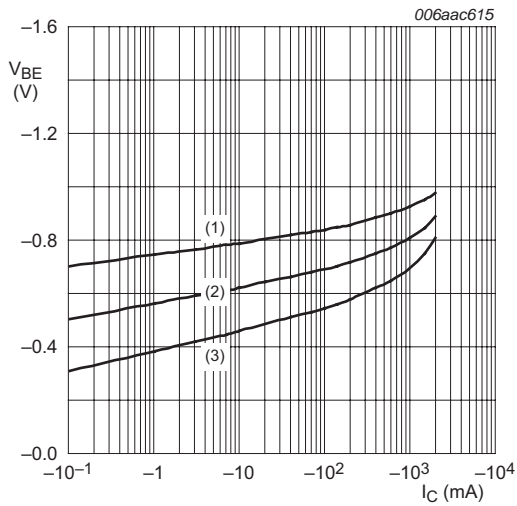
$V_{CEsat} = -5\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 10. PNP transistor: DC current gain as a function of collector current; typical values



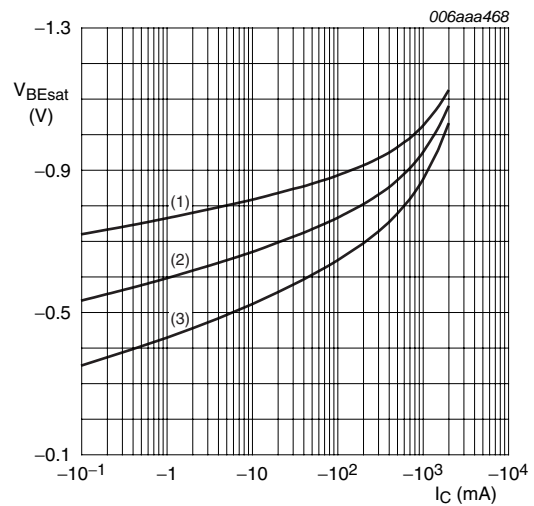
$T_{amb} = 25\text{ °C}$

Fig 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



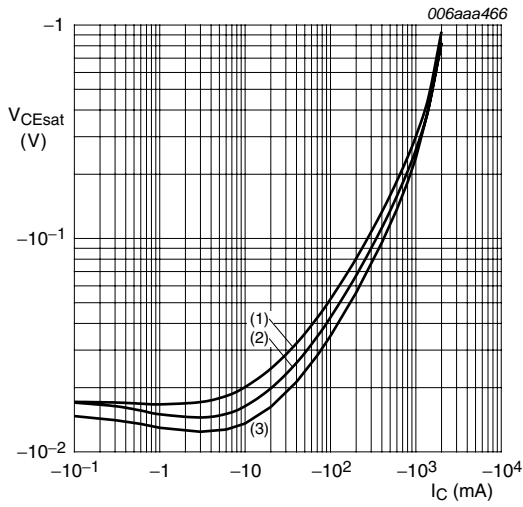
$V_{CEsat} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 12. PNP transistor: Base-emitter voltage as a function of collector current; typical values



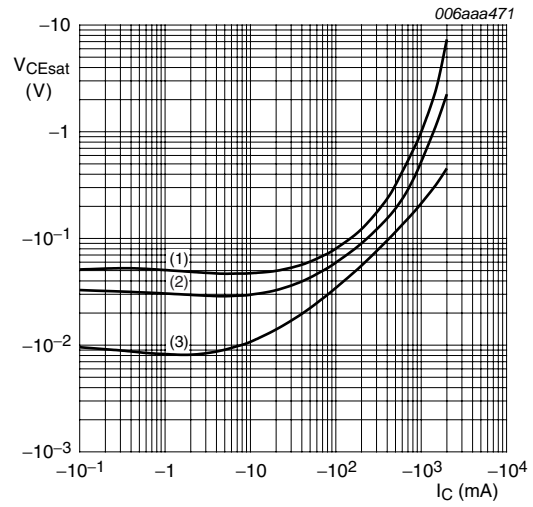
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 13. PNP transistor: Base-emitter saturation voltage as a function of collector current; typical values



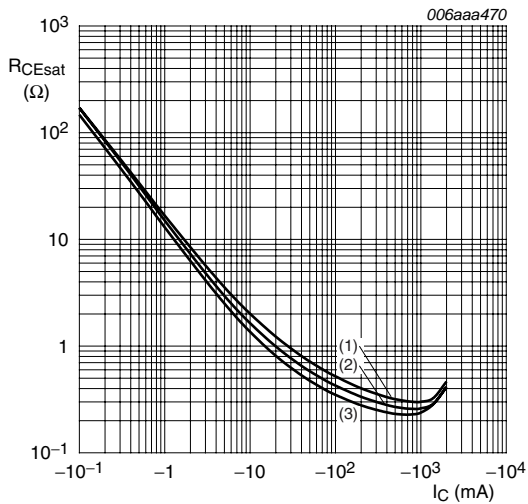
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 14. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



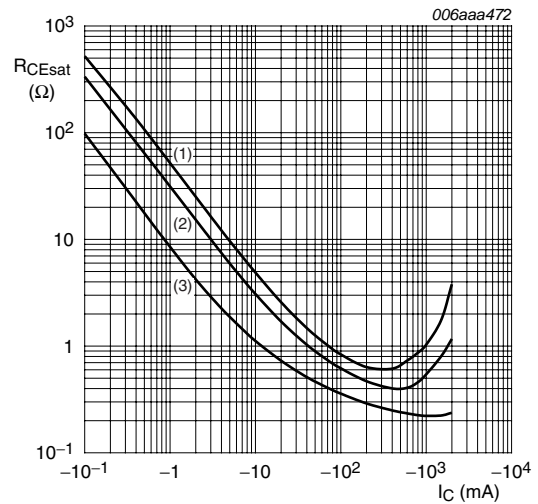
$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 15. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 16. PNP transistor: Collector-emitter saturation resistance as a function of collector current; typical values



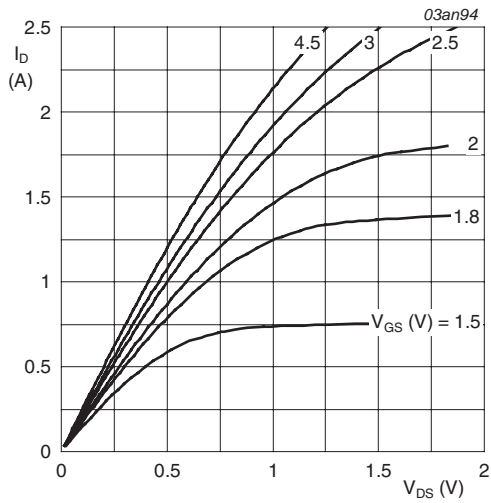
$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 17. PNP transistor: Collector-emitter saturation resistance as a function of collector current; typical values

Table 8. Characteristics for N-channel Trench MOSFET*T_j = 25 °C unless otherwise specified.*

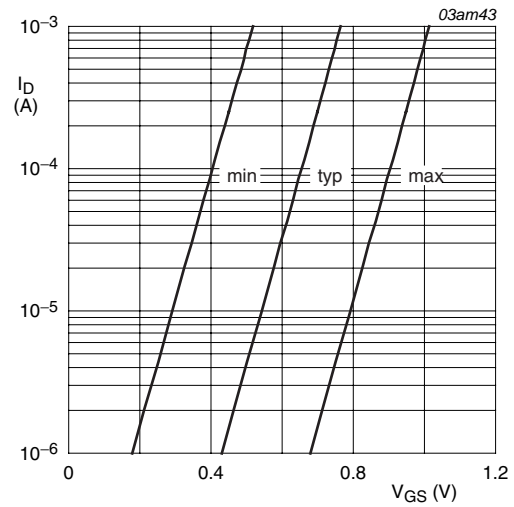
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 10 μA; V _{GS} = 0 V				
		T _j = 25 °C	30	-	-	V
		T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS}				
		T _j = 25 °C	0.45	0.7	0.95	V
		T _j = 150 °C	0.25	-	-	V
		T _j = -55 °C	-	-	1.15	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V				
		T _j = 25 °C	-	-	1	μA
		T _j = 150 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = ±8 V; V _{DS} = 0 V	-	10	±100	nA
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 0.2 A [1]				
		T _j = 25 °C	-	370	580	mΩ
		T _j = 150 °C	-	663	985	mΩ
		V _{GS} = 2.5 V; I _D = 0.1 A	-	440	690	mΩ
		V _{GS} = 1.8 V; I _D = 75 mA	-	540	920	mΩ
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 1 A; V _{DS} = 15 V;	-	0.89	-	nC
Q _{GS}	gate-source charge	V _{GS} = 4.5 V	-	0.1	-	nC
Q _{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V;	-	43	-	pF
C _{oss}	output capacitance	f = 1 MHz	-	7.7	-	pF
C _{rss}	reverse transfer capacitance		-	4.8	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; R _L = 15 Ω;	-	4.0	-	ns
t _r	rise time	V _{GS} = 10 V; R _G = 6 Ω	-	7.5	-	ns
t _{d(off)}	turn-off delay time		-	18	-	ns
t _f	fall time		-	4.5	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 0.3 A; V _{GS} = 0 V	-	0.76	1.2	V

[1] Pulse test: t_p ≤ 300 μs; δ ≤ 0.01.



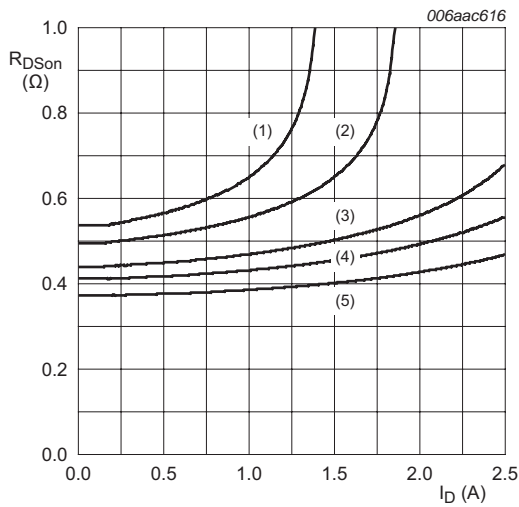
$T_j = 25\text{ }^\circ\text{C}$

Fig 18. MOSFET: Output characteristics: drain current as a function of drain-source voltage; typical values



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

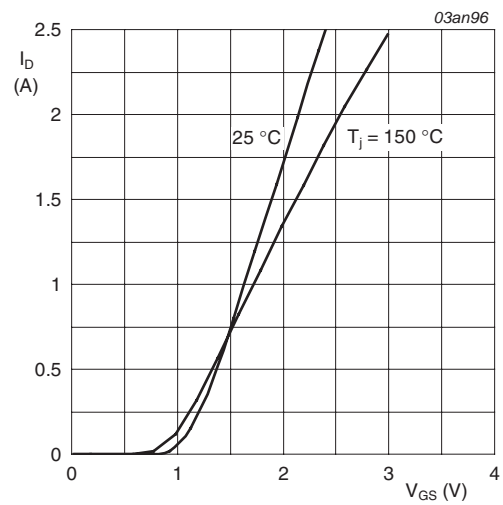
Fig 19. MOSFET: Sub-threshold drain current as a function of gate-source voltage



$T_j = 25\text{ }^\circ\text{C}$

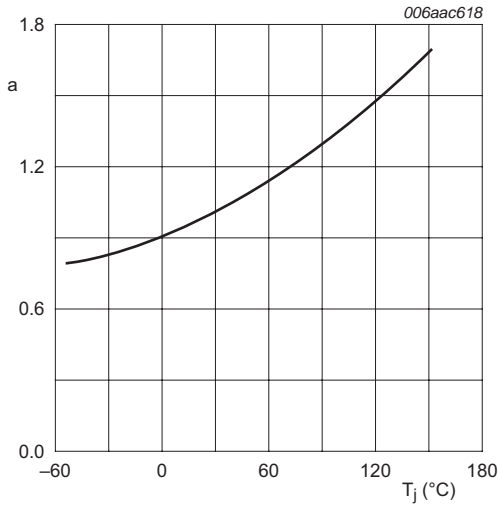
- (1) $V_{GS} = 1.8\text{ V}$
- (2) $V_{GS} = 2.0\text{ V}$
- (3) $V_{GS} = 2.5\text{ V}$
- (4) $V_{GS} = 3.0\text{ V}$
- (5) $V_{GS} = 4.5\text{ V}$

Fig 20. MOSFET: Drain-source on-state resistance as a function of drain current; typical values



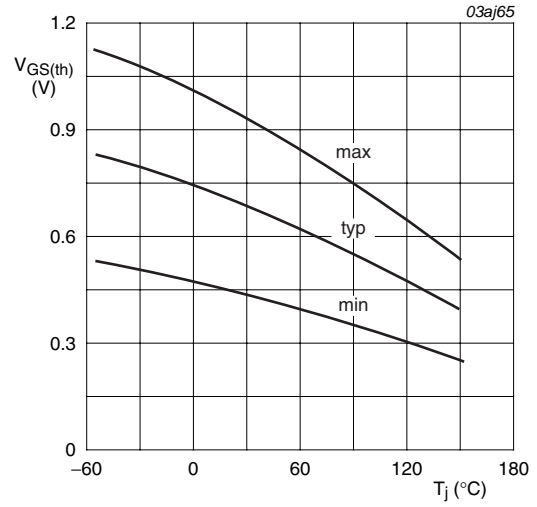
$V_{DS} > I_D \times R_{DSon}$

Fig 21. MOSFET: Transfer characteristics: drain current as a function of gate-source voltage; typical values



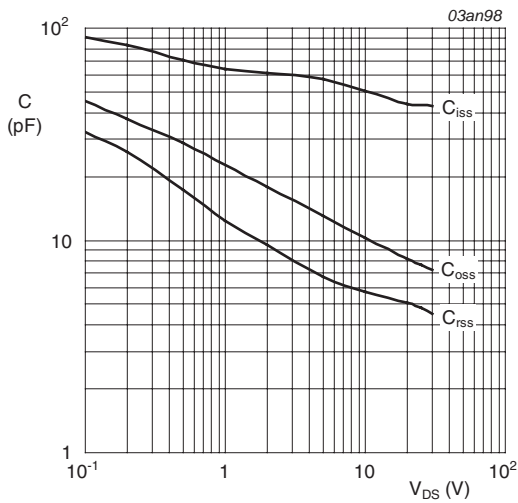
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 22. MOSFET: Normalized drain-source on-state resistance as a function of junction temperature; typical values



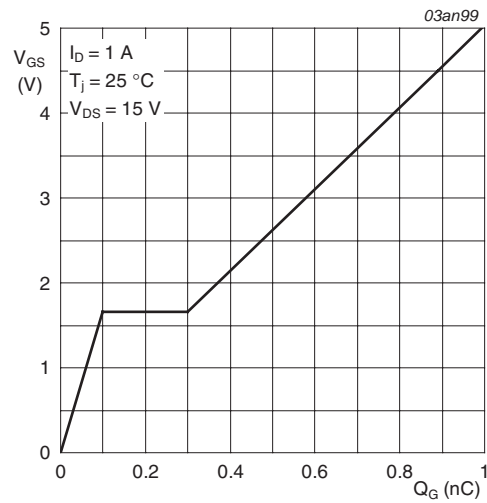
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 23. MOSFET: Gate-source threshold voltage as a function of junction temperature



$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

Fig 24. MOSFET: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 1 \text{ A}$
 $T_j = 25^{\circ} \text{ C}$
 $V_{DS} = 15 \text{ V}$

Fig 25. MOSFET: Gate-source voltage as a function of gate charge; typical values

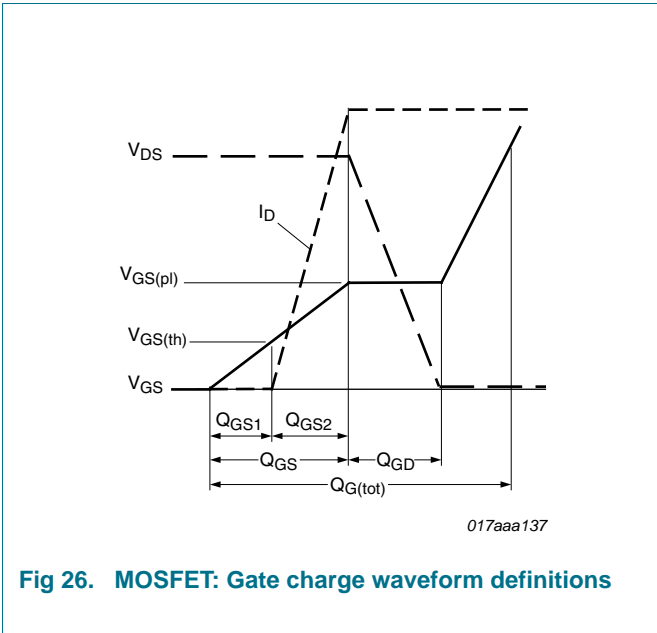


Fig 26. MOSFET: Gate charge waveform definitions

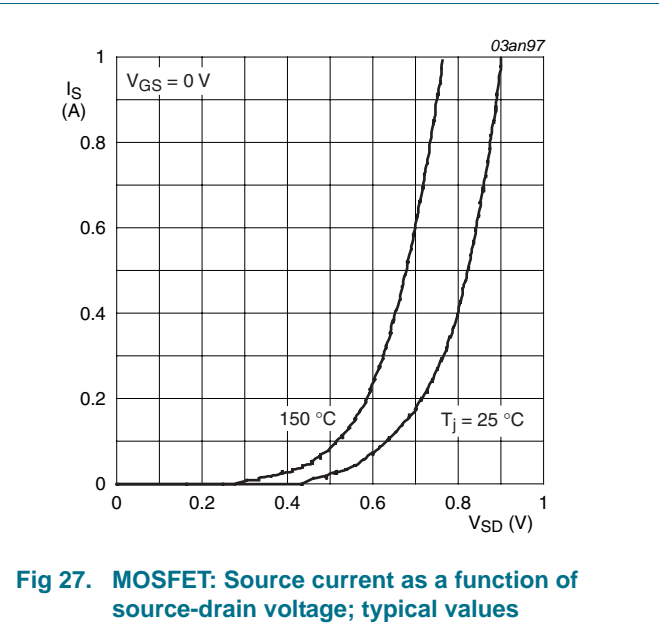


Fig 27. MOSFET: Source current as a function of source-drain voltage; typical values

8. Package outline

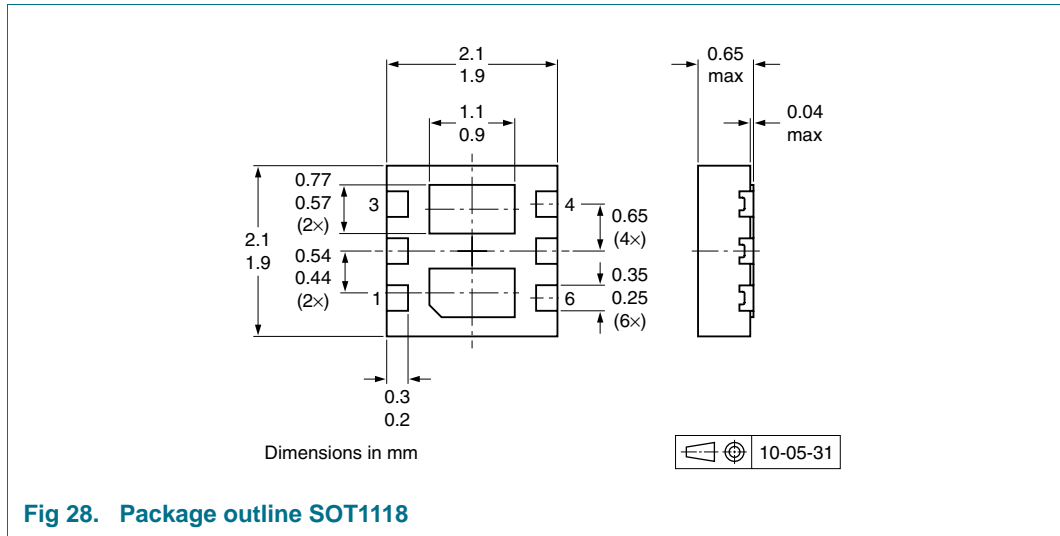


Fig 28. Package outline SOT1118

9. Packing information

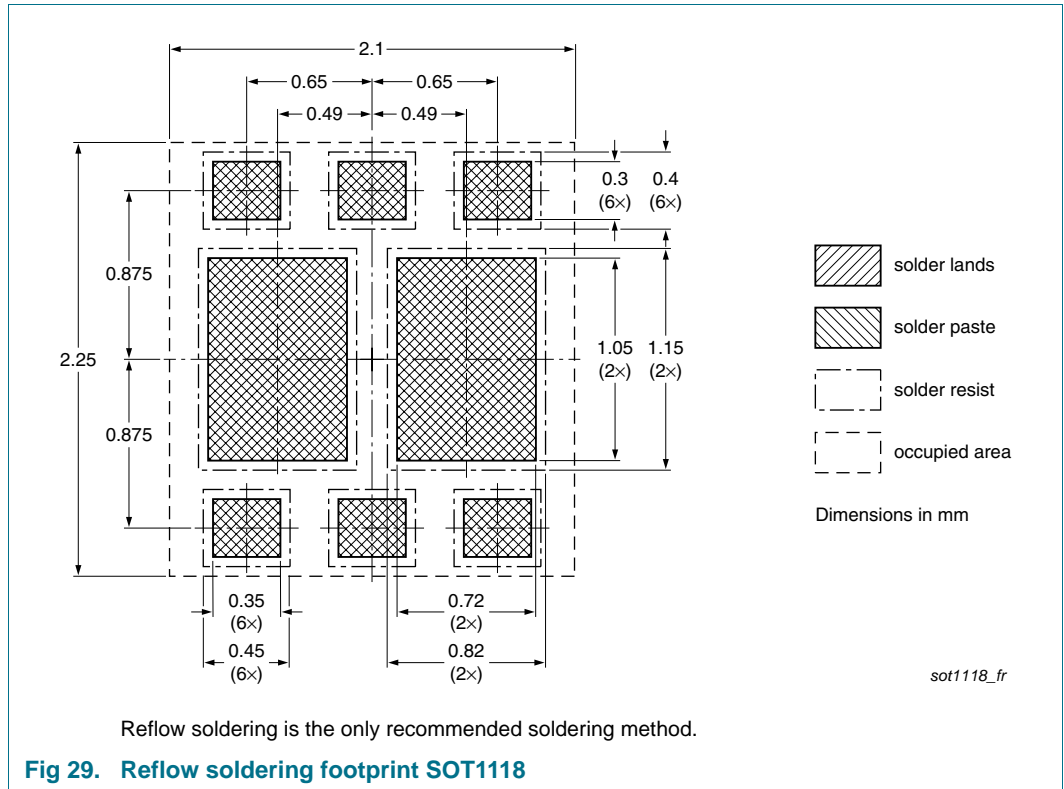
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity
PBSM5240PF	SOT1118	4 mm pitch, 8 mm tape and reel	3000
			-115

[1] For further information and the availability of packing methods, see [Section 13](#).

10. Soldering



11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSM5240PF v.2	20110420	Product data sheet	-	PBSM5240PF v.1
Modifications:		<ul style="list-style-type: none">• Section 1.1 “General description”: updated.• Section 2 “Pinning information”: updated.• Table 1, 5, 6, 7 and 8: updated according to the last measurements.• Figure 1 to 27: added.• Section 12 “Legal information”: updated.		
PBSM5240PF v.1	20100825	Preliminary data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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